

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

1. (Currently Amended) A semiconductor device, comprising:
a polysilicon gate electrode provided on a silicon substrate not including SiGe,

wherein

 said polysilicon gate electrode is subjected to compressive stress as internal stress
therein, to apply tensile stress to said silicon substrate, and
 ions having a mass number of 70 or more are implanted into said polysilicon gate
electrode.

2. (Currently Amended) The semiconductor device according to claim 1, wherein
said polysilicon gate electrode is a gate electrode of an n-channel MOS transistor.

3. (Original) The semiconductor device according to claim 2, wherein
said ions having a mass number of 70 or more are operative to serve as those for
forming a source and drain region of said n-channel MOS transistor.

4. (Original) The semiconductor device according to claim 1, wherein
said ions having a mass number of 70 or more are electrically inactive ions.

5. (Currently Amended) The semiconductor device according to claim 1, wherein
said polysilicon gate electrode has a bird's beak at a lower edge portion thereof, said
bird's beak being defined by a silicon oxide film.

6. (Original) The semiconductor device according to claim 1, wherein
said silicon substrate is a strained silicon substrate.

7-18 (Cancelled).